

MMBTA42 MMBTA43

#### SOT-23

- 1. BASE
- 2. EMITTER
- 3. COLLECTOR



### ■MAXIMUM RATINGS 最大額定値

Characteristic 特性參數	Symbol 符號	MMBTA42	MMBTA43	Unit 單位
Collector-Emitter Voltage 集電極-射極電壓	$V_{\scriptscriptstyle{ ext{CEO}}}$	300	200	Vdc
Collector-Base Voltage 集電極-極電壓	$V_{\scriptscriptstyle CBO}$	300	200	Vdc
Emitter-Base Voltage 發射極基極電壓	$ m V_{EBO}$	6.0	6.0	Vdc
Collector Current-Continuous 集極電流-連續	Ic	500	500	mAdc

### ■THERMAL CHARACTERISTICS 熱特性

Characteristic	Symbol	Max	Unit
特性參數	符號	最大値	單位
Total Device Dissipation 總耗散功率 Board(1)	$P_{D}$	225	mW
T <sub>A</sub> =25℃環境溫度 25℃ Derate above25℃ 超過 25℃遞減		1.8	mW/°C
Thermal Resistance Junction to Ambient 熱阻	$R_{\Theta_{\mathrm{JA}}}$	556	°C/W
Total Device Dissipation 總耗散功率 Alumina Substrate 氧化鋁襯底(2)T <sub>A</sub> =25℃	$P_{\mathrm{D}}$	300	mW
Derate above25℃ 超過 25℃遞減		2.4	mW/°C
Thermal Resistance Junction to Ambient 熱阻	$R_{\Theta JA}$	417	°C/W
Junction and Storage Temperature 結溫和儲存溫度	$T_{\mathrm{J}}$ , $T_{\mathrm{stg}}$	150°C, -55to+150°C	

# ■DEVICE MARKING 打標

MMBTA42=1D MMBTA43=M1E



MMBTA42 MMBTA43

# ■ELECTRICAL CHARACTERISTICS 電特性

(T<sub>A</sub>=25℃ unless otherwise noted 如無特殊說明,溫度爲 25℃)

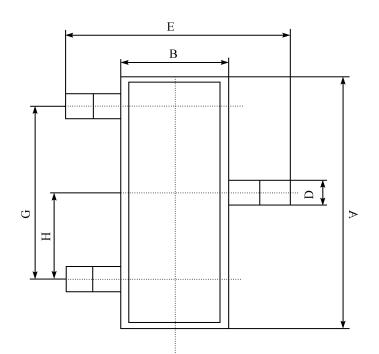
Characteristic	Symbol	Min	Max	Unit
特性參數	符號	最小値	最大値	單位
Collector-Emitter Breakdown Voltage(3) 集電極-射極擊穿電壓(I <sub>C</sub> =1mAdc,I <sub>B</sub> =0)	V <sub>(BR)CEO</sub> MMBTA42 MMBTA43	300 200	_ _	Vdc
Collector-Base Breakdown Voltage 集電極-基極擊穿電壓(I <sub>C</sub> =100µAdc,I <sub>E</sub> =0)	V(BR)CBO MMBTA42 MMBTA43	300 200	_	Vdc
Emitter-Base Breakdown Voltage 發射極-基極擊穿電壓(I <sub>E</sub> = 100µAdc ,I <sub>C</sub> =0)	V <sub>(BR)EBO</sub>	6.0	_	Vdc
Emitter Cutoff Current 發射極截止電流 (V <sub>EB</sub> =6.0Vdc,I <sub>c</sub> =0) (V <sub>EB</sub> =4.0Vdc,I <sub>c</sub> =0)	I <sub>EBO</sub> MMBTA42  MMBTA43	_	100 100	nAdc
Collector Cutoff Current 集電極截止電流 (V <sub>CB</sub> =200Vdc,I <sub>E</sub> =0) (V <sub>CB</sub> =160Vdc,I <sub>E</sub> =0)	I <sub>CBO</sub> MMBTA42 MMBTA43	_	100 100	nAdc
DC Current Gain 直流電流增益	$H_{ m FE}$			
(I <sub>c</sub> =1.0mAdc,V <sub>CE</sub> =10.0Vdc)		25		
$(I_c=10\text{mAdc}, V_{CE}=10.0\text{Vdc})$		40	300	
$(I_c=30\text{mAdc}, V_{CE}=10.0\text{Vdc})$	MMBTA42 MMBTA43	40 40		
Collector-Emitter Saturation Voltage 集電極-發射極飽和壓降 (I <sub>c</sub> =20mAdc, I <sub>B</sub> =2.0mAdc)	V <sub>CE(sat)</sub> MMBTA42 MMBTA43	_	0.5 0.5	Vdc
Base-Emitter Saturation Voltage 基極-發射極飽和壓降 (I <sub>c</sub> =20mAdc, I <sub>B</sub> =2.0mAdc)	V <sub>BE(sat)</sub>	_	0.9	Vdc
Current-Gain-Bandwidth Product 電流增益帶寬乘積 (I <sub>c</sub> =10mAdc,V <sub>CE</sub> =20Vdc,f=100MHz)	$f_{\mathrm{T}}$	50		MHz
Collector-Base Capacitance 輸出電容 (V <sub>CB</sub> =20.0Vdc, I <sub>E</sub> =0, f=1.0MHz)	C <sub>cb</sub> MMBTA42 MMBTA43	_	3.0 4.0	pF

- 1 . FR-5=1.0×0.75×0.062in.
- 2. Alumina=0.4×0.3×0.024in.99.5%alumina.
- 3 . Pulse Width ≤300us;Duty Cycle≤2.0%.

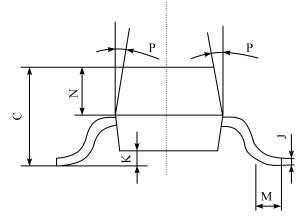


MMBTA42 MMBTA43

### ■DIMENSION 外形封裝尺寸



序號	數值及公差
A	$2.90 \pm 0.10$
В	$1.30\pm0.10$
С	$1.00\pm 0.10$
D	$0.40\pm 0.10$
Е	$2.40\pm0.20$
G	$1.90 \pm 0.10$
Н	$0.95 \pm 0.05$
J	$0.13 \pm 0.05$
K	0.00-0.10
M	≥0.2
N	$0.60\pm0.10$
P	7 ± 2°



This datasheet presents technical data of Tak Cheong's Silicon Rectifier Diodes. Complete specifications for the individual devices are provided in the form of datasheets. A comprehensive Selector Guide is included to simplify the task of choosing the best set of components required for a specific application. For additional information, please visit our website <a href="http://www.takcheong.com">http://www.takcheong.com</a>.

Although information in this datasheet has been carefully checked, no responsibility for the inaccuracies can be assumed by Tak Cheong. Please consult your nearest Tak Cheong's sales office for further assistance.

Tak Cheong reserves the right to make changes without further notice to any products herein to further improve reliability, function or design, cost and productivity.



is registered trademarks of Tak Cheong Electronics (Holdings) Co., Ltd.